

### Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

### Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:  
a silicon substrate; and  
a nickel or iron containing cobalt silicide film formed on said silicon substrate,  
wherein the principal surface of said silicon substrate which is in contact with  
said cobalt silicide film is an Si (111) plane, and the principal surface of said cobalt  
silicide film which is in contact with said Si (111) plane is a  $\text{CoSi}_2$  (111) plane, and  
the ratio of nickel or iron to cobalt in the cobalt silicide film is 0.05 to 50 atomic %.
  
2. (Currently Amended) A The semiconductor device according to claim 1,  
wherein the ratio of nickel or iron to cobalt in the nickel or iron containing cobalt  
silicide film is 0.05 to 50 18 atomic %.
  
3. (Currently Amended) A process for producing a semiconductor device  
comprising the steps of:  
forming a gate electrode on a silicon substrate;  
forming a diffusion layer(s) on said silicon substrate;  
forming a cobalt film in contact with the upper side of at least said gate  
electrode or said diffusion layer(s);  
depositing at least a nickel film or an iron film on said cobalt film; and  
forming a nickel or iron containing cobalt silicide film on at least said gate  
electrode or said diffusion layer(s);

wherein the principal surface of said silicon substrate is in an Si (111) plane.

4. (Currently Amended) The process according to claim 3, wherein the concentration of nickel or iron in the nickel or iron containing cobalt silicide film is 0.05 to 50 atomic % based on cobalt.
5. (New) The process according to claim 3, wherein the concentration of nickel or iron in the nickel or iron containing cobalt silicide film is 0.05 to 18 atomic % based on cobalt.
6. (New) The semiconductor device according to claim 1, wherein the nickel or iron is present in the nickel or iron containing cobalt silicide film in the form of nickel or iron silicide or as single bodies of nickel or iron.
7. (New) The semiconductor device according to claim 6, wherein the nickel or iron is present in the nickel or iron containing cobalt silicide film in the form of single bodies of nickel or iron.
8. (New) The semiconductor device according to claim 2, wherein the nickel or iron is present in the nickel or iron containing cobalt silicide film in the form of nickel or iron silicide or as single bodies of nickel or iron.
9. (New) The semiconductor device according to claim 8, wherein the nickel or iron is present in the nickel or iron containing cobalt silicide film in the form of single bodies of nickel or iron.